500 mW DO-35 Hermetically Sealed Glass Zener Voltage Regulators

This is a complete series of 500 mW Zener diodes with limits and excellent operating characteristics that reflect the superior capabilities of silicon–oxide passivated junctions. All this in an axial–lead hermetically sealed glass package that offers protection in all common environmental conditions.

Specification Features:

- Zener Voltage Range 2.4 V to 20 V
- ESD Rating of Class 3 (>16 KV) per Human Body Model
- DO–204AH (DO–35) Package Smaller than Conventional DO–204AA Package
- Double Slug Type Construction
- Metallurgical Bonded Construction

Mechanical Characteristics:

CASE: Double slug type, hermetically sealed glass **FINISH:** All external surfaces are corrosion resistant and leads are readily solderable

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES:

230°C, 1/16" from the case for 10 seconds **POLARITY:** Cathode indicated by polarity band **MOUNTING POSITION:** Any

MAXIMUM RATINGS (Note 1.)

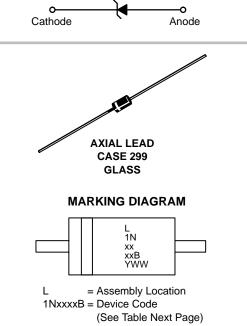
Rating	Symbol	Value	Unit
Max. Steady State Power Dissipation @ $T_1 \le 75^{\circ}C$, Lead Length = 3/8"	PD	500	mW
Derate above 75°C		4.0	mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	65 to +200	°C

1. Some part number series have lower JEDEC registered ratings.



ON Semiconductor[™]

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Y = Year WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping		
1NxxxxB	Axial Lead	3000 Units/Box		
1NxxxxBRL	Axial Lead	5000/Tape & Reel		
1NxxxxBRL2 *	Axial Lead	5000/Tape & Reel		
1NxxxxBTA	Axial Lead	5000/Ammo Pack		
1NxxxxBTA2 *	Axial Lead	5000/Tape & Reel		
1NxxxxBRR1 [†]	Axial Lead	3000/Tape & Reel		
1NxxxxBRR2 [‡]	Axial Lead	3000/Tape & Reel		

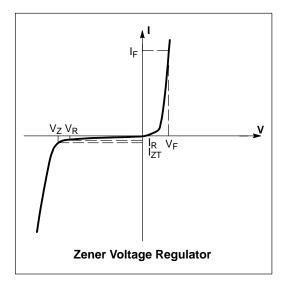
* The "2" suffix refers to 26 mm tape spacing.

[†] Polarity band **up** with cathode lead off first

[‡] Polarity band **down** with cathode lead off first

Devices listed in *bold, italic* are ON Semiconductor **Preferred** devices. **Preferred** devices are recommended choices for future use and best overall value. **ELECTRICAL CHARACTERISTICS** ($T_L = 30^{\circ}C$ unless otherwise noted, $V_F = 1.5$ V Max @ $I_F = 100$ mA for all types)

Symbol	Parameter
Vz	Reverse Zener Voltage @ IZT
I _{ZT}	Reverse Current
Z _{ZT}	Maximum Zener Impedance @ I _{ZT}
I _{ZK}	Reverse Current
Z _{ZK}	Maximum Zener Impedance @ I _{ZK}
I _R	Reverse Leakage Current @ V _R
V _R	Breakdown Voltage
١ _F	Forward Current
V _F	Forward Voltage @ I _F
I _{ZM}	Maximum DC Zener Current



ELECTRICAL CHARACTERISTICS (T_L = 30°C unless otherwise noted, V_F = 1.5 V Max @ I_F = 100 mA for all types)

		Ze	ener Volta	ge (Note 3	3.)	Zener Impedance (Note 4.)			Leakage	I _{ZM}	
Device Device		V _Z (Volts)		@ І _{ст}	Z _{ZT} @ ե _{ZT} Z _{ZK} @ ե _{ZK}		I _R @ V _R		(Note 5.)		
(Note 2.)	Marking	Min	Nom	Max	mA	Ω	Ω	mA	μΑ	Volts	mA
1N5985B	1N5985B	2.28	2.4	2.52	5	100	1800	0.25	100	1.0	208
1N5987B	1N5987B	2.85	3.0	3.15	5	95	2000	0.25	50	1.0	167
1N5988B	1N5988B	3.13	3.3	3.46	5	95	2200	0.25	25	1.0	152
1N5990B	1N5990B	3.7	3.9	4.09	5	90	2400	0.25	10	1.0	128
1N5991B	1N5991B	4.08	4.3	4.51	5	88	2500	0.25	5.0	1.0	116
1N5992B	1N5992B	4.46	4.7	4.93	5	70	2200	0.25	3.0	1.5	106
1N5993B	1N5993B	4.84	5.1	5.35	5	50	2050	0.25	2.0	2.0	98
1N5994B	1N5994B	5.32	5.6	5.88	5	25	1800	0.25	2.0	3.0	89
1N5995B	1N5995B	5.89	6.2	6.51	5	10	1300	0.25	1.0	4.0	81
1N5996B	1N5996B	6.46	6.8	7.14	5	8.0	750	0.25	1.0	5.2	74
1N5997B	1N5997B	7.12	7.5	7.87	5	7.0	600	0.25	0.5	6.0	67
1N5998B	1N5998B	7.79	8.2	8.61	5	7.0	600	0.25	0.5	6.5	61
1N5999B	1N5999B	8.64	9.1	9.55	5	10	600	0.25	0.1	7.0	55
1N6000B	1N6000B	9.5	10	10.5	5	15	600	0.25	0.1	8.0	50
1N6001B	1N6001B	10.45	11	11.55	5	18	600	0.25	0.1	8.4	45
1N6002B	1N6002B	11.4	12	12.6	5	22	600	0.25	0.1	9.1	42
1N6004B	1N6004B	14.25	15	15.75	5	32	600	0.25	0.1	11	33
1N6007B	1N6007B	19	20	21	5	48	600	0.25	0.1	15	25

2. TOLERANCE AND VOLTAGE DESIGNATION

Tolerance designation – Device tolerance of $\pm 5\%$ is indicated by a "B" suffix.

3. ZENER VOLTAGE (VZ) MEASUREMENT

The zener voltage is measured with the device junction in the thermal equilibrium at the lead temperature (T_L) at 30°C ± 1°C and 3/8″ lead length.

4. ZENER IMPEDANCE (ZZ) DERIVATION

 Z_{ZT} and Z_{ZK} are measured by dividing the ac voltage drop across the device by the ac current applied. The specified limits are for $I_{Z(ac)} = 0.1 I_{Z(dc)}$ with the ac frequency = 1.0 kHz.

5. MAXIMUM ZENER CURRENT RATINGS (IZM)

This data was calculated using nominal voltages. The maximum current handling capability on a worst case basis is limited by the actual zener voltage at the operation point and the power derating curve.

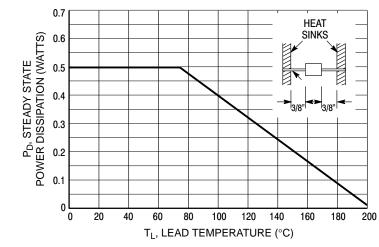


Figure 1. Steady State Power Derating

APPLICATION NOTE — ZENER VOLTAGE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature, T_L, should be determined from:

$$T_{L} = \theta_{LA} P_{D} + T_{A}.$$

 θ_{LA} is the lead-to-ambient thermal resistance (°C/W) and P_D is the power dissipation. The value for θ_{LA} will vary and depends on the device mounting method. θ_{LA} is generally 30 to 40°C/W for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the lead can also be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_L , the junction temperature may be determined by:

$$\mathsf{T}_{\mathsf{J}} = \mathsf{T}_{\mathsf{L}} + \Delta \mathsf{T}_{\mathsf{J}\mathsf{L}}.$$

 ΔT_{JL} is the increase in junction temperature above the lead temperature and may be found from Figure 2 for dc power:

$$\Delta T_{JL} = \theta_{JL} P_D.$$

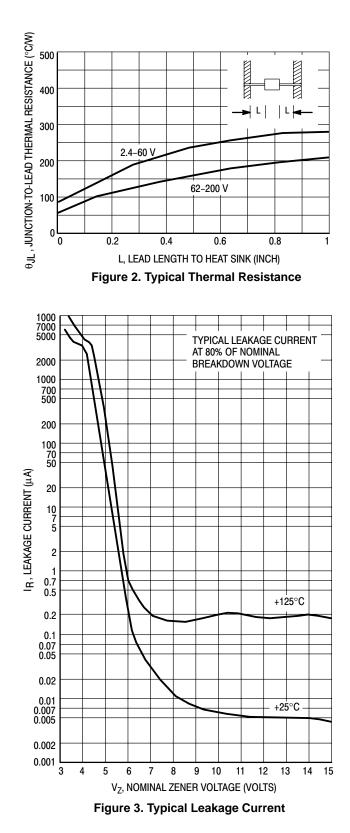
For worst-case design, using expected limits of I_Z , limits of P_D and the extremes of $T_J(\Delta T_J)$ may be estimated. Changes in voltage, V_Z , can then be found from:

$$\Delta \mathsf{V} = \theta_{\mathsf{VZ}}\mathsf{T}_{\mathsf{J}}.$$

 $\theta_{VZ},$ the zener voltage temperature coefficient, is found from Figures 4 and 5.

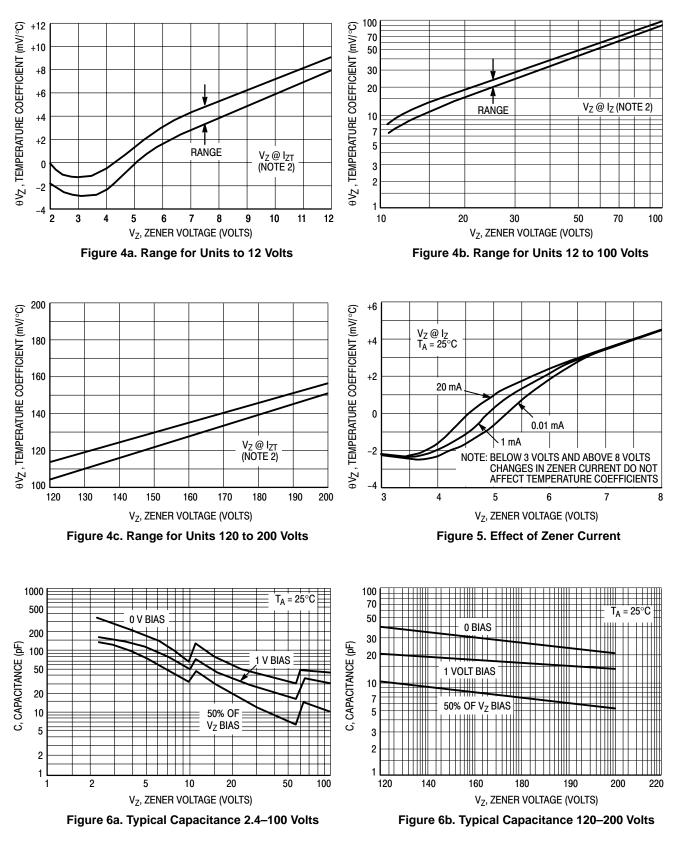
Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Surge limitations are given in Figure 7. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots, resulting in device degradation should the limits of Figure 7 be exceeded.





(-55°C to +150°C temperature range; 90% of the units are in the ranges indicated.)



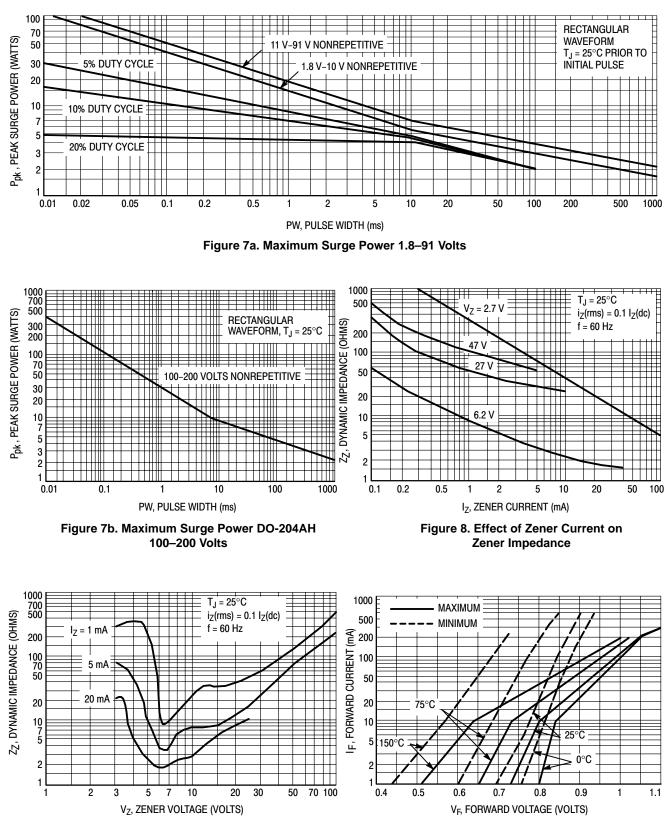
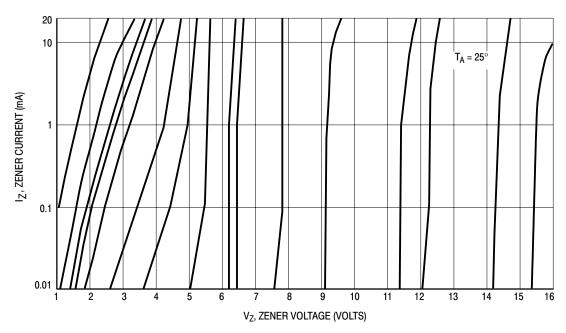


Figure 9. Effect of Zener Voltage on Zener Impedance

Figure 10. Typical Forward Characteristics





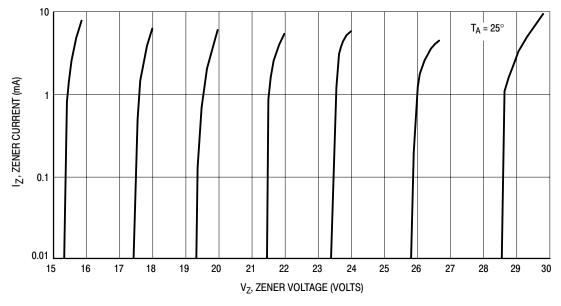


Figure 12. Zener Voltage versus Zener Current — V_Z = 15 thru 30 Volts

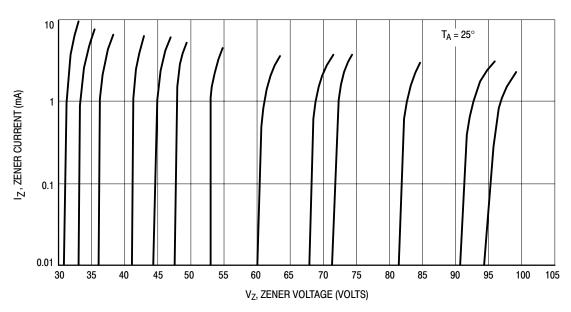


Figure 13. Zener Voltage versus Zener Current — $V_Z = 30$ thru 105 Volts

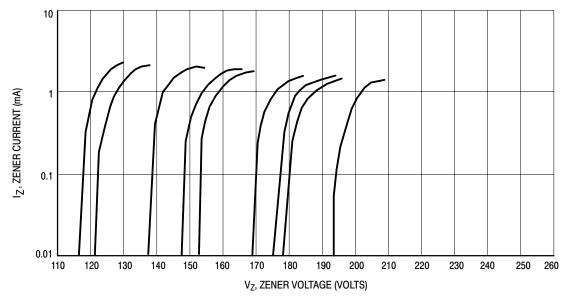


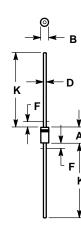
Figure 14. Zener Voltage versus Zener Current — V_Z = 110 thru 220 Volts

OUTLINE DIMENSIONS

Zener Voltage Regulators – Axial Leaded

500 mW DO-35 Glass

GLASS DO-35/D0-204AH CASE 299-02 **ISSUE A**



NOTES:

- NOTES: 1. PACKAGE CONTOUR OPTIONAL WITHIN A AND B HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT NOT SUBJECT TO THE MINIMUM LIMIT OF B. 2. LEAD DIAMETER NOT CONTROLLED IN ZONE F TO ALLOW FOR FLASH, LEAD FINISH BUILDUP AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS. 3. POLARITY DEMOTED BY CATHODE BAND
- 3. POLARITY DENOTED BY CATHODE BAND. 4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	3.05	5.08	0.120	0.200	
В	1.52	2.29	0.060	0.090	
D	0.46	0.56	0.018	0.022	
F		1.27		0.050	
K	25.40	38.10	1.000	1.500	

All JEDEC dimensions and notes apply.

<u>Notes</u>

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